

(TLP747G)

- OFFICE MACHINE.
- HOUSEHOLD USE EQUIPMENT.
- SOLID STATE RELAY.
- SWITCHING POWER SUPPLY.

The TOSHIBA TLP747G consists of a photo-thyristor optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP package.

- Peak Off-State Voltage : 400V (Min.)
- Trigger LED Current : 15mA (Max.)
- On-State Current : 150mA (Max.)
- UL Recognized : UL1577, File No. E67349
- BSI Approved : BS415 : 1990, BS7002 : 1989 (EN60950)  
Certificate No. 7364, 7365
- SEMKO Approved : SS4330784  
Certificate No. 9203174
- Isolation Voltage : 4000Vrms (Min.)
- Option (D4) type  
VDE Approved : DIN VDE0884 / 08.87,  
Certificate No. 74286

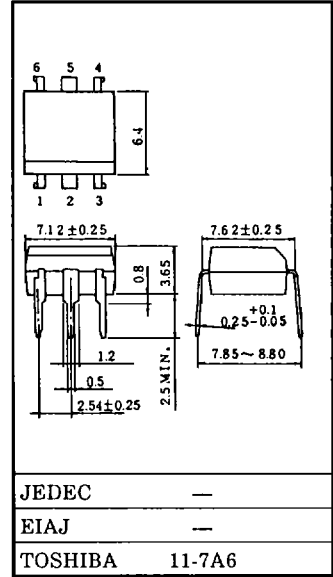
Maximum Operating Insulation Voltage : 630V<sub>PK</sub>

Highest Permissible Over Voltage : 6000V<sub>PK</sub>

(Note) When a VDE0884 approved type is needed, please designate the "Option (D4)"

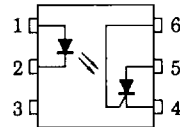
- |                        | 7.62mm pitch<br>standard type | 10.16mm pitch<br>TLP×××F type |
|------------------------|-------------------------------|-------------------------------|
| • Creepage Distance :  | 7.0mm (Min.)                  | 8.0mm (Min.)                  |
| Clearance :            | 7.0mm (Min.)                  | 8.0mm (Min.)                  |
| Insulation Thickness : | 0.5mm (Min.)                  | 0.5mm (Min.)                  |

Unit in mm



Weight : 0.42g

PIN CONFIGURATIONS (TOP VIEW)



- 1 : ANODE
- 2 : CATHODE
- 3 : NC
- 4 : CATHODE
- 5 : ANODE
- 6 : GATE

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MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
I <sub>DF</sub>	Forward Current	I <sub>F</sub>	60	mA
	Forward Current Derating (Ta ≥ 39°C)	ΔI <sub>F</sub> /°C	-0.7	mA/°C
	Peak Forward Current (100μs pulse, 100pps)	I <sub>FP</sub>	1	A
	Reverse Voltage	V <sub>R</sub>	5	V
	Junction Temperature	T <sub>j</sub>	125	°C
E <sub>ETC</sub> D <sub>ETC</sub>	Peak Forward Voltage (R <sub>GK</sub> = 27kΩ)	V <sub>DRM</sub>	400	V
	Peak Reverse Voltage (R <sub>GK</sub> = 27kΩ)	V <sub>RRM</sub>	400	V
	On-State Current	I <sub>T(RMS)</sub>	150	mA
	On-State Current Derating (Ta ≥ 25°C)	ΔI <sub>T</sub> /°C	-2.0	mA/°C
	Peak On-State Current (100μs pulse, 120pps)	I <sub>TP</sub>	3	A
	Peak One Cycle Surge Current	I <sub>TSM</sub>	2	A
	Peak Reverse Gate Voltage	V <sub>GPM</sub>	5	V
	Power Dissipation	P <sub>D</sub>	150	mW
	Power Dissipation Derating (Ta ≥ 25°C)	ΔP <sub>D</sub> /°C	-2.0	mW/°C
	Junction Temperature	T <sub>j</sub>	100	°C
Storage Temperature Range	T <sub>stg</sub>	-55~125	°C	
Operating Temperature Range	T <sub>opr</sub>	-40~100	°C	
Lead Soldering Temperature (10 sec.)	T <sub>sold</sub>	260	°C	
Total Package Power Dissipation	P <sub>T</sub>	250	mW	
Total Package Power Dissipation Derating (Ta ≥ 25°C)	ΔP <sub>T</sub> /°C	-3.3	mW/°C	
Isolation Voltage (AC, 1min., R.H. < 60%)	(NOTE) BV <sub>S</sub>	4000	V <sub>rms</sub>	

Note : Device considered a two terminal device : pins 1, 2 and 3 shorted together, and pins 4, 5 and 6 shorted together.

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INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
LED	Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = 10mA	1.0	1.15	1.3	V	
	Reverse Current	I <sub>R</sub>	V <sub>R</sub> = 5V	—	—	10	μA	
	Capacitance	C <sub>T</sub>	V = 0, f = 1MHz	—	30	—	pF	
ELECTR	Off-State Current	I <sub>DRM</sub>	V <sub>AK</sub> = 400V R <sub>GK</sub> = 27kΩ	Ta = 25°C	—	10	5000	nA
				Ta = 100°C	—	1	100	μA
	Reverse Current	I <sub>RRM</sub>	V <sub>KA</sub> = 400V R <sub>GK</sub> = 27kΩ	Ta = 25°C	—	10	5000	nA
				Ta = 100°C	—	1	100	μA
	On-State Voltage	V <sub>TM</sub>	I <sub>TM</sub> = 100mA	—	0.9	1.3	V	
	Holding Current	I <sub>H</sub>	R <sub>GK</sub> = 27kΩ	—	0.2	—	mA	
	Off-State dv/dt	dv/dt	V <sub>AK</sub> = 280V, R <sub>GK</sub> = 27kΩ	5	10	—	V/μs	
Capacitance	C <sub>j</sub>	V = 0, f = 1MHz Anode to Gate Gate to Cathode	—	20	—	pF		
			—	350	—			

COUPLED CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Trigger LED Current	I <sub>FT</sub>	V <sub>AK</sub> = 6V, R <sub>GK</sub> = 27kΩ	—	—	15	mA
Turn-on Time	t <sub>on</sub>	I <sub>F</sub> = 30mA, V <sub>AA</sub> = 50V R <sub>GK</sub> = 27kΩ	—	10	—	μs
Coupled dv/dt	dv/dt	V <sub>S</sub> = 500V, R <sub>GK</sub> = 27kΩ	500	—	—	V/μs
Capacitance(Input to Output)	C <sub>S</sub>	V <sub>S</sub> = 0, f = 1MHz	—	0.8	—	pF
Isolation Resistance	R <sub>S</sub>	V <sub>S</sub> = 500V, R.H. ≤ 60%	5 × 10 <sup>10</sup>	10 <sup>14</sup>	—	Ω
Isolation Voltage	BV <sub>S</sub>	AC, 1 minute	4000	—	—	V <sub>rms</sub>
		AC, 1 second, in oil	—	10000	—	
		DC, 1 minute, in oil	—	10000	—	V <sub>dc</sub>

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V <sub>AC</sub>	—	—	120	V <sub>ac</sub>
Forward Current	I <sub>F</sub>	20	—	25	mA
Operating Temperature	T <sub>opr</sub>	-25	—	85	°C
Gate to Cathode Resistance	R <sub>GK</sub>	—	27	33	kΩ
Gate to Cathode Capacity	C <sub>GK</sub>	—	0.01	0.1	μF

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